

INA280 2.7-V to 120-V, 1.1-MHz, High Precision Current Sense Amplifier in Small (SC-70) Package

1 Features

- Wide common-mode voltage:
 - Operational voltage: 2.7 V to 120 V
 - Survival voltage: -20 V to +122 V
- Excellent CMRR:
 - 120-dB DC (Minimum)
 - 85-dB AC at 50 kHz
- Accuracy
 - Gain:
 - Gain error: $\pm 0.5\%$ (maximum)
 - Gain drift: ± 20 ppm/ $^{\circ}\text{C}$ (maximum)
 - Offset:
 - Offset voltage: ± 150 μV (maximum)
 - Offset drift: ± 1 $\mu\text{V}/^{\circ}\text{C}$ (maximum)
- Available gains:
 - INA280A1: 20 V/V
 - INA280A2: 50 V/V
 - INA280A3: 100 V/V
 - INA280A4: 200 V/V
 - INA280A5: 500 V/V
- High bandwidth: 1.1 MHz
- Slew rate: 2 V/ μs
- Quiescent current: 370 μA

2 Applications

- Active antenna system mMIMO (AAS)
- Macro remote radio unit (RRU)
- 48-V rack server
- 48-V merchant network & server power supply
- Test and measurement

3 Description

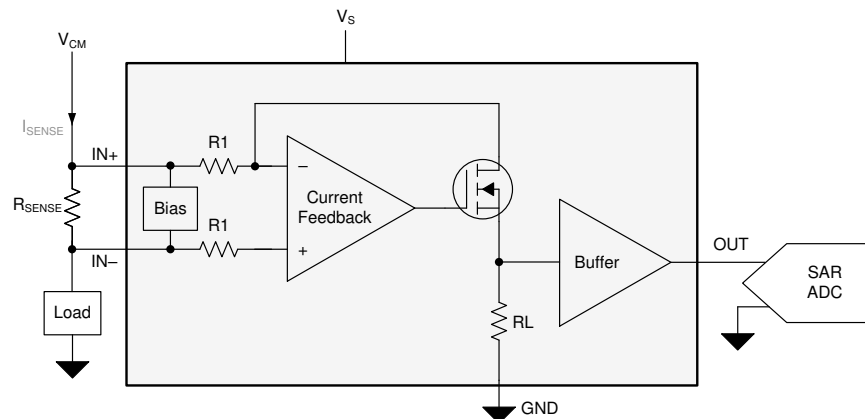
The INA280 is a current sense amplifier that can measure voltage drops across shunt resistors over a wide common-mode range from 2.7 V to 120 V. It is in a highly space-efficient SC-70 package with a PCB footprint of only 2.0 mm \times 2.1 mm. The current measurement accuracy is achieved thanks to the combination of an ultra-low offset voltage of ± 150 μV (maximum), a small gain error of $\pm 0.5\%$ (maximum), and a high DC CMRR of 140 dB (typical). The INA280 is not only designed for DC current measurement, but also for high-speed applications (like fast overcurrent protection, for example) with a high bandwidth of 1.1 MHz (at gain of 20 V/V) and an 85-dB AC CMRR (at 50 kHz).

The INA280 operates from a single 2.7-V to 20-V supply and draws a 370- μA supply current (typical). The INA280 available with five gain options: 20 V/V, 50 V/V, 100 V/V, 200 V/V, and 500 V/V. The low offset and drift of the INA280 enables accurate current sensing over the extended operating temperature range of -40°C to $+125^{\circ}\text{C}$.

Device Information

PART NUMBER	PACKAGE ⁽¹⁾	BODY SIZE (NOM)
INA280	SC-70 (5)	2.00 mm \times 1.25 mm

- (1) For all available packages, see the package option addendum at the end of the data sheet.



Typical Application



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
October 2020	*	Initial Release

5 Pin Configuration and Functions

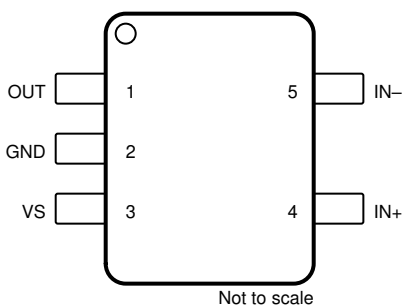


Figure 5-1. DCK Package 5-Pin SC-70 Top View

Pin Functions

PIN		TYPE	DESCRIPTION
NAME	NO.		
GND	2	Ground	Ground
IN–	5	Input	Connect to load side of shunt resistor
IN+	4	Input	Connect to supply side of shunt resistor
OUT	1	Output	Output voltage
VS	3	Power	Power supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _S	Supply Voltage	−0.3	22	V
Analog Inputs, V _{IN+} , V _{IN−} ⁽²⁾	Differential (V _{IN+}) − (V _{IN−})	−30	30	V
	Common - mode	−20	122	V
Output		GND − 0.3	V _S + 0.3	V
T _A	Operating Temperature	−55	150	°C
T _J	Junction temperature		150	°C
T _{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) V_{IN+} and V_{IN−} are the voltages at the V_{IN+} and V_{IN−} pins, respectively.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins ⁽¹⁾	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{CM}	Common-mode input range ⁽¹⁾	V _S	48	120	V
V _S	Operating supply range	2.7	5	20	V
T _A	Ambient temperature	−40		125	°C

- (1) Common-mode voltage can go below V_S under certain conditions. See [Figure 7-1](#) for additional information on operating range.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		INA280	UNIT
		DCK (SC-70)	
		5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	191.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	144.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	69.2	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	46.2	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	69.0	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

at $T_A = 25\text{ }^{\circ}\text{C}$, $V_S = 5\text{ V}$, $V_{\text{SENSE}} = V_{\text{IN}+} - V_{\text{IN}-} = 0.5\text{ V} / \text{Gain}$, $V_{\text{CM}} = V_{\text{IN}-} = 48\text{ V}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
INPUT						
CMRR	Common-mode rejection ratio	$V_{CM} = 2.7\text{ V to }120\text{ V}$, $T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$	120	140		dB
		$f = 50\text{ kHz}$		85		
V_{os}	Offset voltage, input referred			15	± 150	μV
dV_{os}/dT	Offset voltage drift	$T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$			1	$\mu\text{V}/^{\circ}\text{C}$
PSRR	Power supply rejection ratio, input referred	$V_S = 2.7\text{ V to }20\text{ V}$, $T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$		1	± 10	$\mu\text{V/V}$
I_B	Input bias current	I_{B+} , $V_{SENSE} = 0\text{ mV}$	10	20	30	μA
		I_{B-} , $V_{SENSE} = 0\text{ mV}$	10	20	30	
OUTPUT						
G	Gain	A1 devices		20		V/V
		A2 devices		50		
		A3 devices		100		
		A4 devices		200		
		A5 devices		500		
	Gain error	$\text{GND} + 50\text{ mV} \leq V_{OUT} \leq V_S - 200\text{ mV}$		0.1	± 0.5	%
	Gain error drift	$T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$		2.5	20	$\text{ppm}/^{\circ}\text{C}$
	Nonlinearity error			0.01		%
	Maximum capacitive load	No sustained oscillations, no isolation resistor		500		pF
VOLTAGE OUTPUT						
	Swing to V_S power supply rail	$R_{LOAD} = 10\text{ k}\Omega$, $T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$		$V_S - 0.07$	$V_S - 0.2$	V
	Swing to ground	$R_{LOAD} = 10\text{ k}\Omega$, $V_{SENSE} = 0\text{ V}$, $T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$		0.005	0.025	V
FREQUENCY RESPONSE						
BW	Bandwidth	A1 devices, $C_{LOAD} = 5\text{ pF}$, $V_{SENSE} = 200\text{ mV}$		1100		kHz
		A2 devices, $C_{LOAD} = 5\text{ pF}$, $V_{SENSE} = 80\text{ mV}$		1100		
		A3 devices, $C_{LOAD} = 5\text{ pF}$, $V_{SENSE} = 40\text{ mV}$		900		
		A4 devices, $C_{LOAD} = 5\text{ pF}$, $V_{SENSE} = 20\text{ mV}$		850		
		A5 devices, $C_{LOAD} = 5\text{ pF}$, $V_{SENSE} = 8\text{ mV}$		800		
SR	Slew rate			2		V/ μs
	Settling time	$V_{OUT} = 4\text{ V} \pm 0.1\text{ V}$ step, output settles to 0.5%		9		μs
		$V_{OUT} = 4\text{ V} \pm 0.1\text{ V}$ step, output settles to 1%		5		
NOISE						
V_{e_n}	Voltage noise density			50		$\text{nV}/\sqrt{\text{Hz}}$
POWER SUPPLY						
V_S	Supply voltage	$T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$	2.7		20	V
I_Q	Quiescent current			370	500	μA
		$T_A = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$			600	

6.6 Typical Characteristics

All specifications at $T_A = 25^\circ\text{C}$, $V_S = 5\text{ V}$, $V_{\text{SENSE}} = V_{\text{IN}+} - V_{\text{IN}-} = 0.5\text{ V} / \text{Gain}$, and $V_{\text{CM}} = V_{\text{IN}-} = 48\text{ V}$, unless otherwise noted.

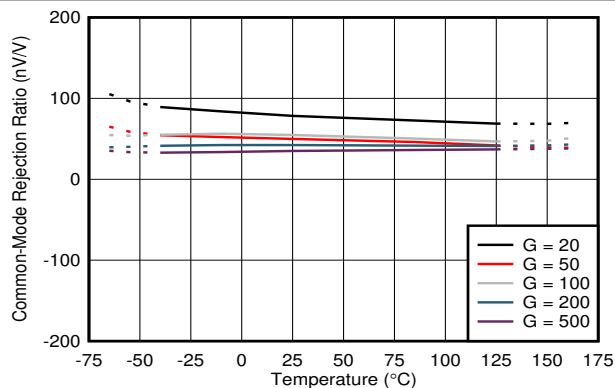


Figure 6-1. Common-Mode Rejection Ratio vs Temperature

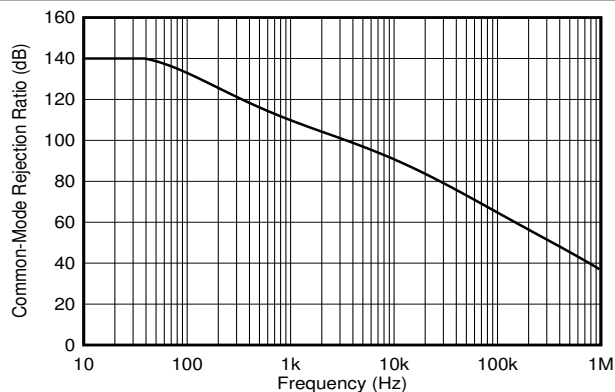


Figure 6-2. Common-Mode Rejection Ratio vs Frequency

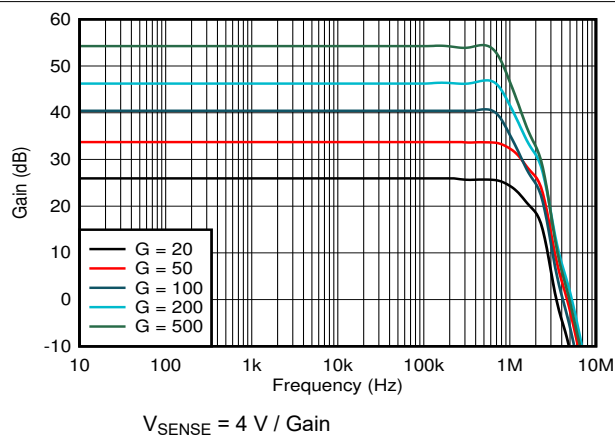


Figure 6-3. Gain vs Frequency

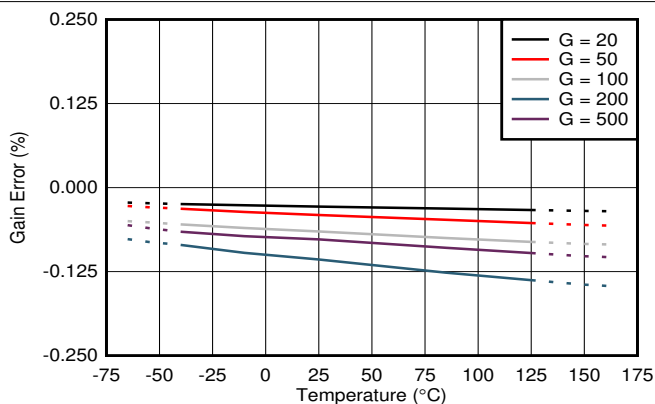


Figure 6-4. Gain Error vs Temperature

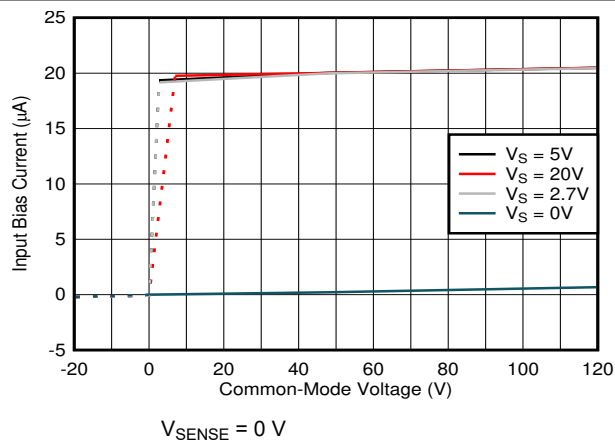


Figure 6-5. Input Bias Current vs Common-Mode Voltage

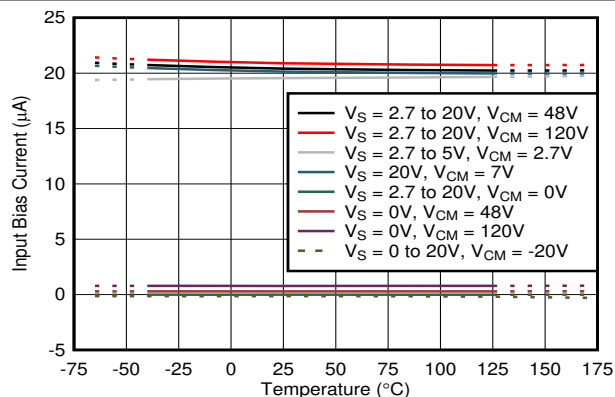


Figure 6-6. Input Bias Current vs Temperature

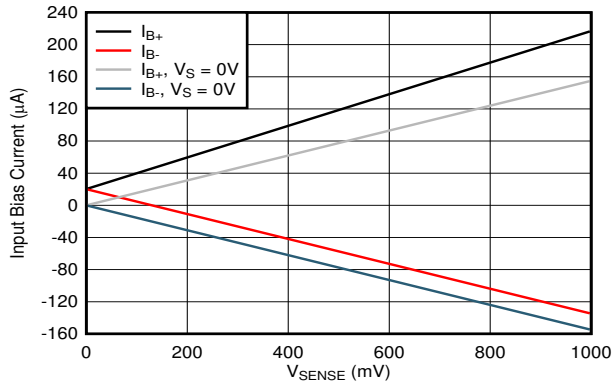


Figure 6-7. Input Bias Current vs V_{SENSE} , A1 devices

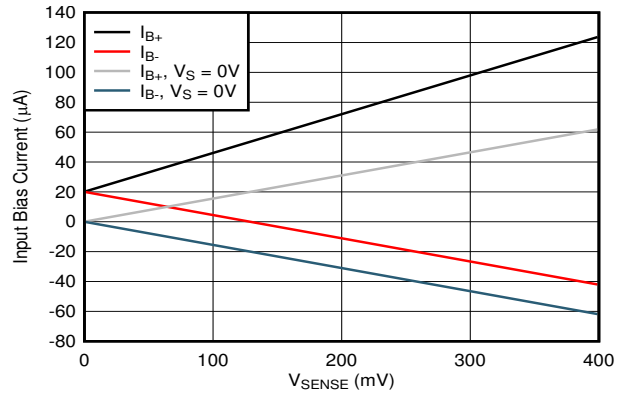


Figure 6-8. Input Bias Current vs V_{SENSE} , A2 and A3 devices

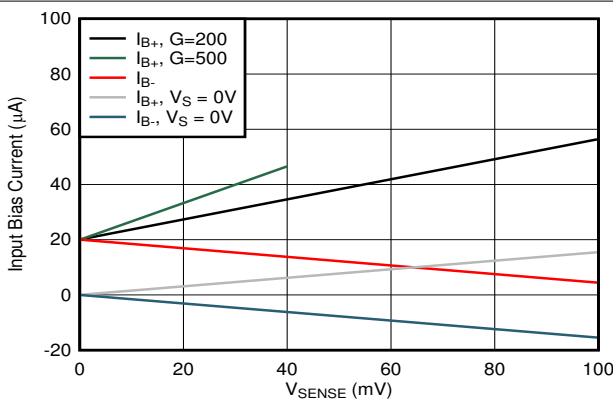


Figure 6-9. Input Bias Current vs V_{SENSE} , A4 and A5 devices

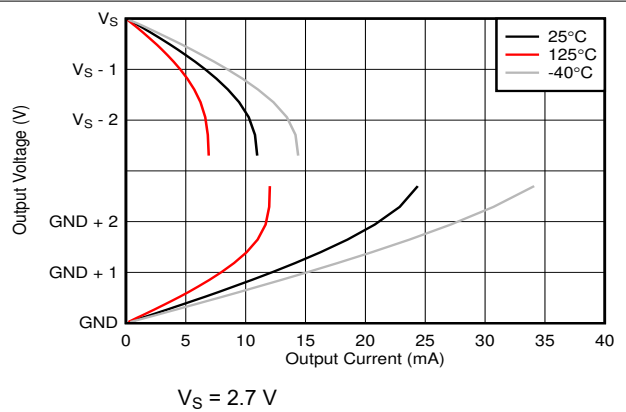


Figure 6-10. Output Voltage vs Output Current

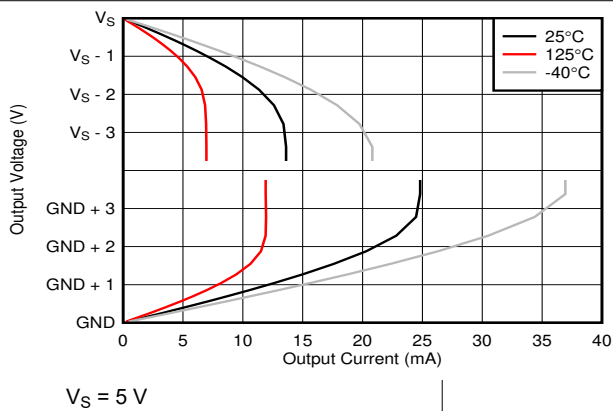


Figure 6-11. Output Voltage vs Output Current

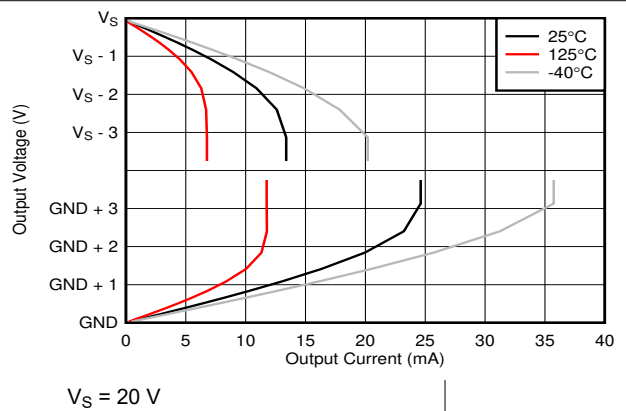
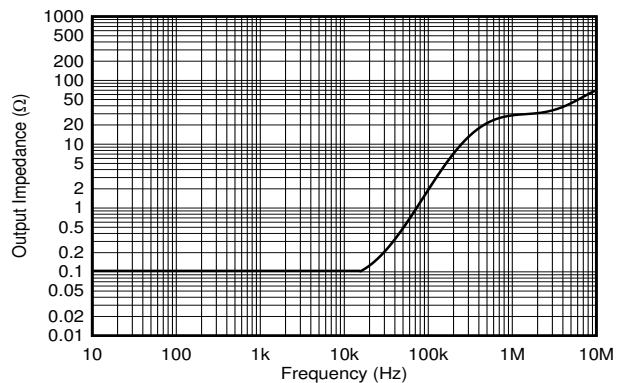
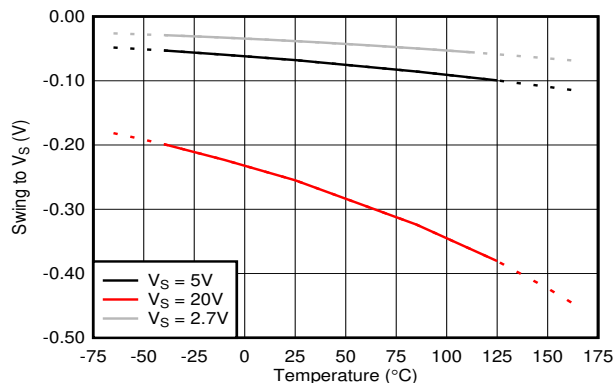
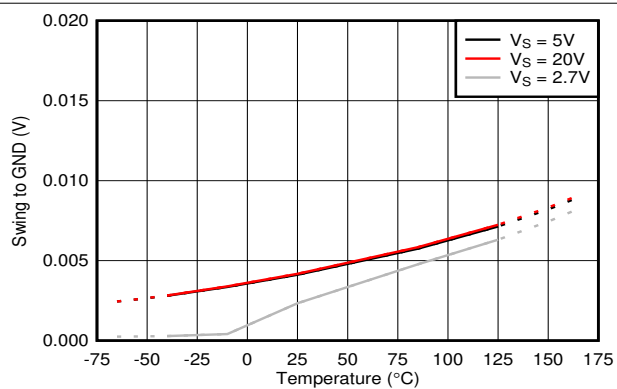
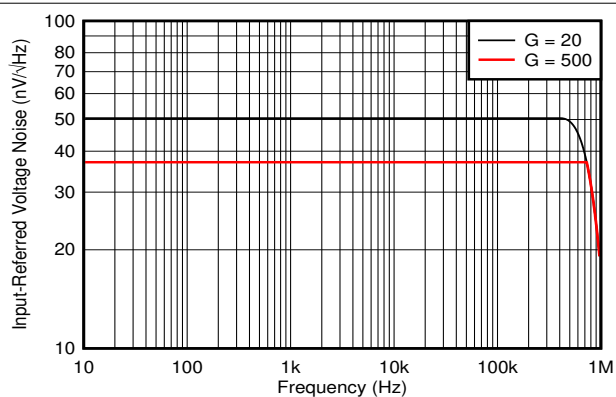
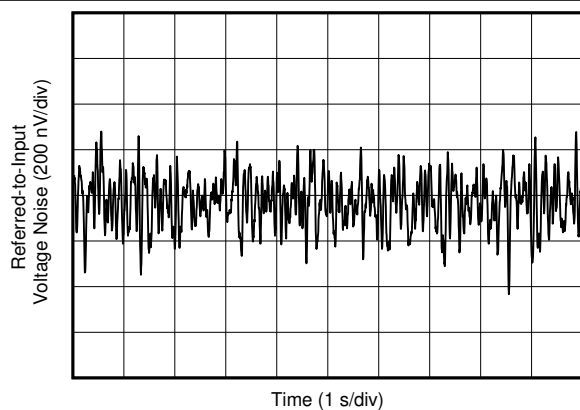
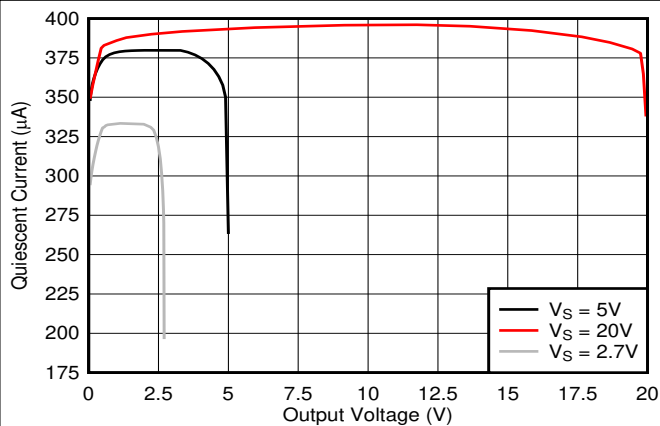


Figure 6-12. Output Voltage vs Output Current


Figure 6-13. Output Impedance vs Frequency

 $R_L = 10\text{ k}\Omega$
Figure 6-14. Swing to Supply vs Temperature

 $R_L = 10\text{ k}\Omega$
Figure 6-15. Swing to GND vs Temperature

Figure 6-16. Input Referred Noise vs Frequency

Figure 6-17. Input Referred Noise

Figure 6-18. Quiescent Current vs Output Voltage

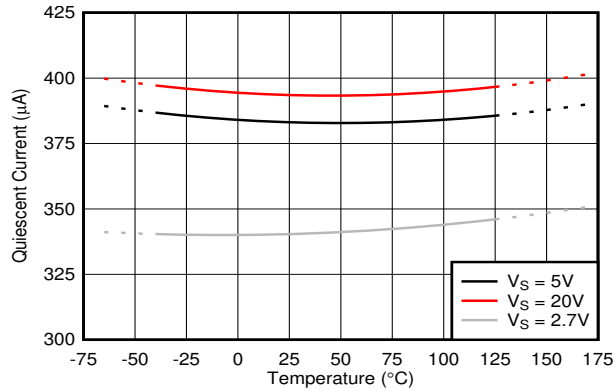


Figure 6-19. Quiescent Current vs Temperature

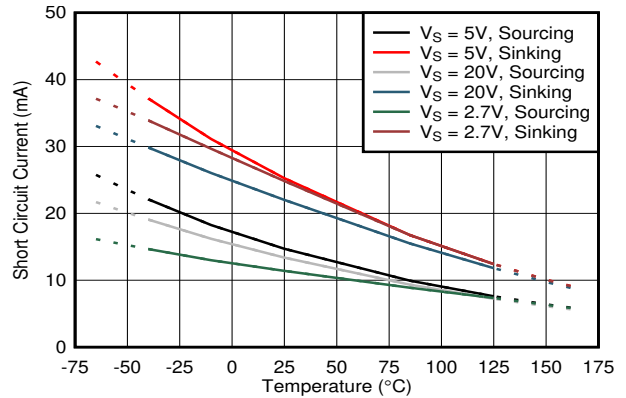


Figure 6-20. Short-Circuit Current vs Temperature

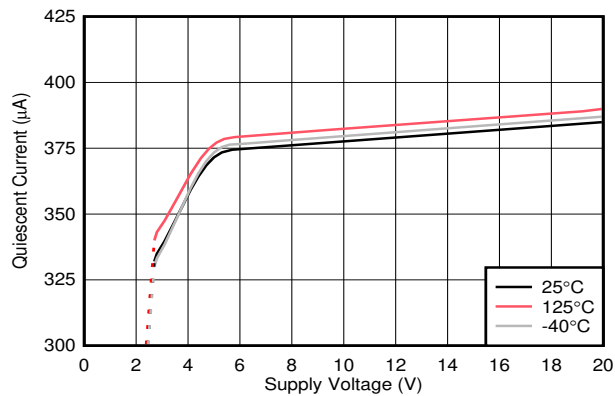


Figure 6-21. Quiescent Current vs Supply Voltage

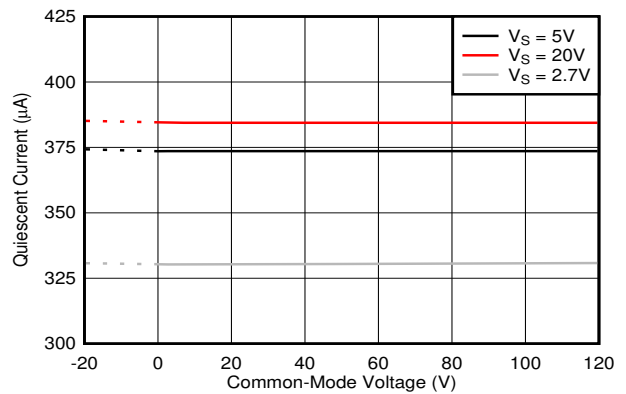


Figure 6-22. Quiescent Current vs Common-Mode Voltage

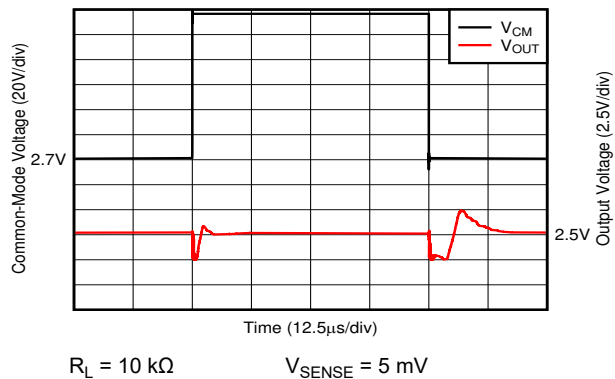


Figure 6-23. Common-Mode Voltage Fast Transient Pulse, A5 devices

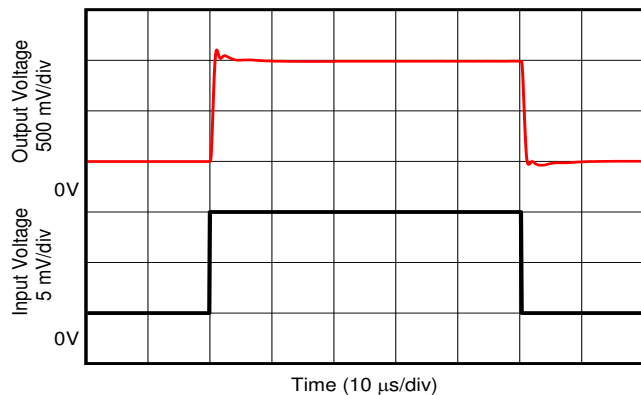
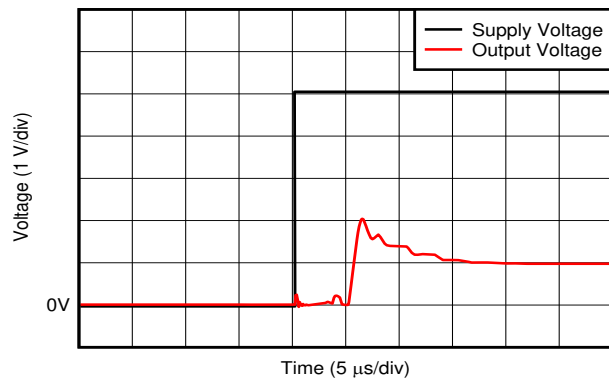
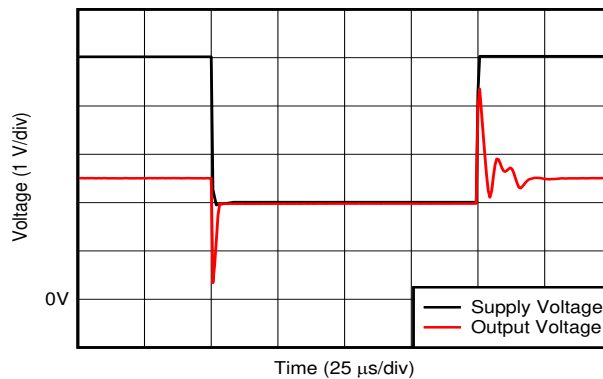


Figure 6-24. Step Response, A3 devices



$V_{\text{SENSE}} = 0 \text{ mV}$

Figure 6-25. Start-Up Response



$V_{\text{SENSE}} = 5 \text{ mV}$

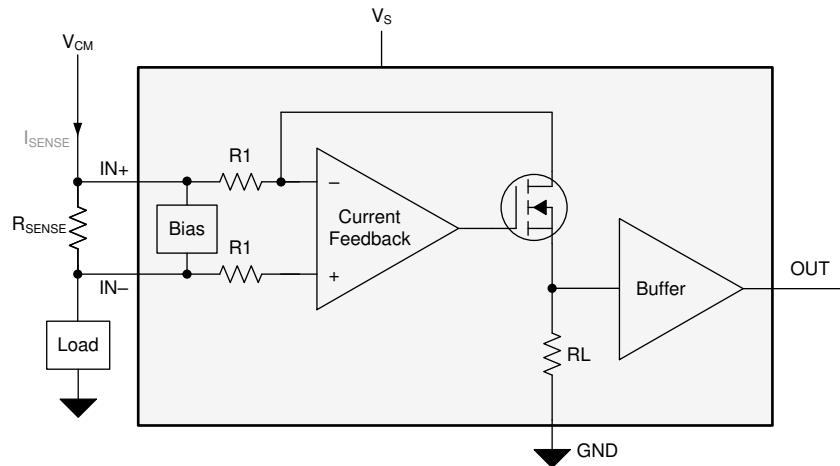
Figure 6-26. Supply Transient Response, A5 devices

7 Detailed Description

7.1 Overview

The INA280 is a high-side only current-sense amplifier that offers a wide common-mode range, excellent common-mode rejection ratio (CMRR), high bandwidth, and fast slew rate. Different gain versions are available to optimize the output dynamic range based on the application. The INA280 is designed using a transconductance architecture with a current-feedback amplifier that enables low bias currents of 20 μA and a common-mode voltage of 120 V.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Amplifier Input Common-Mode Range

The INA280 supports large input common-mode voltages from 2.7 V to 120 V and features a high DC CMRR of 140 dB (typical) and a 85-dB AC CMRR at 50 kHz. The minimum common-mode voltage is restricted by the supply voltage as shown in Figure 7-1. The topology of the internal amplifiers INA280 restricts operation to high-side, current-sensing applications.

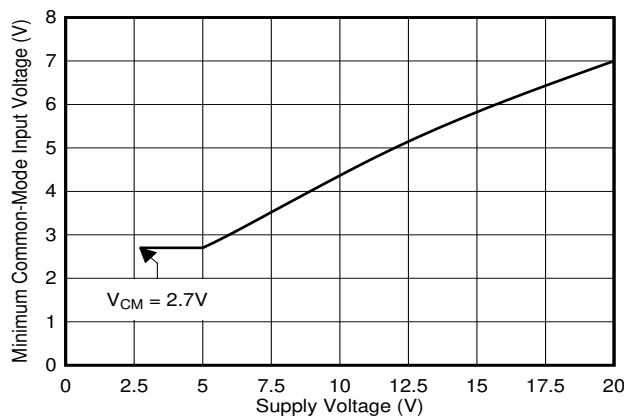


Figure 7-1. Minimum Common-Mode Voltage vs Supply

7.3.1.1 Input-Signal Bandwidth

The INA280 –3-dB bandwidth is gain dependent with several gain options of 20 V/V, 50 V/V, 100 V/V, 200 V/V, and 500 V/V as shown in Figure 6-2. The unique multistage design enables the amplifier to achieve high bandwidth at all gains. This high bandwidth provides the throughput and fast response that is required for the rapid detection and processing of overcurrent events.

The bandwidth of the device also depends on the applied V_{SENSE} voltage. Figure 7-2 shows the bandwidth performance profile of the device over frequency as output voltage increases for each gain variation. As shown in Figure 7-2, the device exhibits the highest bandwidth with higher V_{SENSE} voltages, and the bandwidth is higher with lower device gain options. Individual requirements determine the acceptable limits of error for high-frequency, current-sensing applications. Testing and evaluation in the end application or circuit is required to determine the acceptance criteria and validate whether or not the performance levels meet the system specifications.

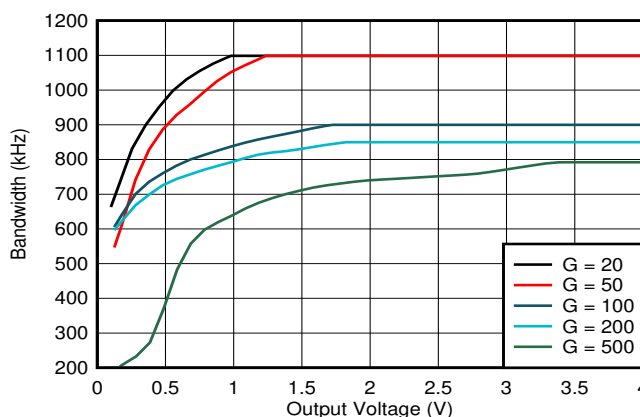


Figure 7-2. Bandwidth vs Output Voltage

7.3.1.2 Low Input Bias Current

The INA280 input bias current draws 20 μ A (typical) even with common-mode voltages as high as 120 V. This enables precision current sensing in applications where the sensed current is small or applications that require lower input leakage current.

7.3.1.3 Multiple Fixed Gain Outputs

The INA280 gain error is < 0.5% at room temperature for all gain options, with a maximum drift of 20ppm/°C over the full temperature range of –40 °C to +125 °C. The INA280 is available in multiple gain options of 20 V/V, 50 V/V, 100 V/V, 200 V/V, and 500 V/V, which the system designer should select based on their desired signal-to-noise ratio and other system requirements.

The INA280 closed-loop gain is set by a precision, low-drift internal resistor network. Even though the ratio of these resistors are well matched, the absolute value of these resistors may vary significantly. TI does not recommend adding additional resistance around the INA280 to change the effective gain because of this variation, however. The typical values of the gain resistors are described in Table 7-1.

Table 7-1. Fixed Gain Resistor

GAIN	R1	RL
20 (V/V)	25 k Ω	500 k Ω
50 (V/V)	10 k Ω	500 k Ω
100 (V/V)	10 k Ω	1000 k Ω
200 (V/V)	5 k Ω	1000 k Ω
500 (V/V)	2 k Ω	1000 k Ω

7.3.1.4 Wide Supply Range

The INA280 operates with a wide supply range from a 2.7 V to 20 V. The output stage supports a full-scale output voltage range of up to V_S . Wide output range can enable very-wide dynamic range current measurements. For a gain of 20 V/V, the maximum differential input acceptable is 1 V.

7.4 Device Functional Modes

7.4.1 Unidirectional Operation

The INA280 measures the differential voltage developed by current flowing through a resistor that is commonly referred to as a current-sensing resistor or a current-shunt resistor. The INA280 operates in unidirectional mode only, meaning it only senses current sourced from a power supply to a system load as shown in [Figure 7-3](#).

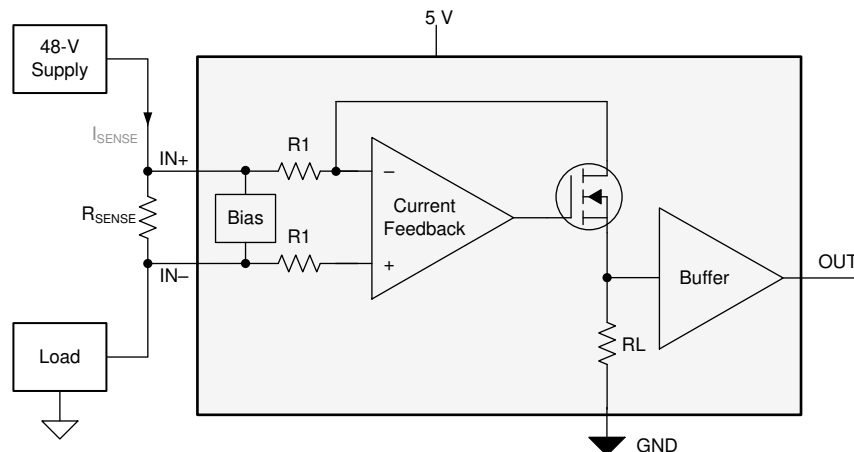


Figure 7-3. Unidirectional Application

The linear range of the output stage is limited to how close the output voltage can approach ground under zero-input conditions. The zero current output voltage of the INA280 is very small, with a maximum of GND + 25 mV. Make sure to apply a sense voltage of (25 mV / Gain) or greater to keep the INA280 output in the linear region of operation.

7.4.2 High Signal Throughput

With a bandwidth of 1.1 MHz at a gain of 20 V/V and a slew rate of 2 V/ μ s, the INA280 is specifically designed for detecting and protecting applications from fast inrush currents. As shown in [Table 7-2](#), the INA280 responds in less than 2 μ s for a system measuring a 75-A threshold on a 2-m Ω shunt.

Table 7-2. Response Time

PARAMETER		EQUATION	INA280 AT $V_S = 5\text{ V}$
G	Gain		20 V/V
I_{MAX}	Maximum current		100 A
$I_{Threshold}$	Threshold current		75 A
R_{SENSE}	Current sense resistor value		2 m Ω
V_{OUT_MAX}	Output voltage at maximum current	$V_{OUT} = I_{MAX} \times R_{SENSE} \times G$	4 V
V_{OUT_THR}	Output voltage at threshold current	$V_{OUT_THR} = I_{THR} \times R_{SENSE} \times G$	3 V
SR	Slew rate		2 V/ μ s
	Output response time	$T_{response} = V_{OUT_THR} / SR$	< 2 μ s

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The INA280 amplifies the voltage developed across a current-sensing resistor as current flows through the resistor to the load. The wide input common-mode voltage range and high common-mode rejection of the INA280 allows use over a wide range of voltage rails while still maintaining an accurate current measurement.

8.1.1 R_{SENSE} and Device Gain Selection

The accuracy of any current-sense amplifier is maximized by choosing the current-sense resistor to be as large as possible. A large sense resistor maximizes the differential input signal for a given amount of current flow and reduces the error contribution of the offset voltage. However, there are practical limits as to how large the current-sense resistor can be in a given application because of the resistor size and maximum allowable power dissipation. Equation 1 gives the maximum value for the current-sense resistor for a given power dissipation budget:

$$R_{\text{SENSE}} < \frac{PD_{\text{MAX}}}{I_{\text{MAX}}^2} \quad (1)$$

where:

- PD_{MAX} is the maximum allowable power dissipation in R_{SENSE} .
- I_{MAX} is the maximum current that will flow through R_{SENSE} .

An additional limitation on the size of the current-sense resistor and device gain is due to the power-supply voltage, V_S , and device swing-to-rail limitations. To make sure that the current-sense signal is properly passed to the output, both positive and negative output swing limitations must be examined. Equation 2 provides the maximum values of R_{SENSE} and GAIN to keep the device from exceeding the positive swing limitation.

$$I_{\text{MAX}} \times R_{\text{SENSE}} \times \text{GAIN} < V_{\text{SP}} \quad (2)$$

where:

- I_{MAX} is the maximum current that will flow through R_{SENSE} .
- GAIN is the gain of the current-sense amplifier.
- V_{SP} is the positive output swing as specified in the data sheet.

To avoid positive output swing limitations when selecting the value of R_{SENSE} , there is always a trade-off between the value of the sense resistor and the gain of the device under consideration. If the sense resistor selected for the maximum power dissipation is too large, then it is possible to select a lower-gain device in order to avoid positive swing limitations.

The negative swing limitation places a limit on how small the sense resistor value can be for a given application. Equation 3 provides the limit on the minimum value of the sense resistor.

$$I_{\text{MIN}} \times R_{\text{SENSE}} \times \text{GAIN} > V_{\text{SN}} \quad (3)$$

where:

- I_{MIN} is the minimum current that will flow through R_{SENSE} .
- GAIN is the gain of the current-sense amplifier.

- V_{SN} is the negative output swing of the device.

The measurement error expected from the additional external filter resistors can be calculated using Equation 4, where the gain error factor is calculated using Equation 5.

$$\text{Gain Error (\%)} = 100 \times (\text{Gain Error Factor} - 1) \quad (4)$$

The gain error factor, shown in Equation 4, can be calculated to determine the gain error introduced by the additional external series resistance. Equation 4 calculates the deviation of the shunt voltage, resulting from the attenuation and imbalance created by the added external filter resistance. Table 8-2 provides the gain error factor and gain error for several resistor values.

$$\text{Gain Error Factor} = \frac{R_B \times R_1}{(R_B \times R_1) + (R_B \times R_{IN}) + (2 \times R_{IN} \times R_1)} \quad (5)$$

Where:

- R_{IN} is the external filter resistance value.
- R_1 is the INA280 input resistance value specified in Table 7-1.
- R_B is the internal bias resistance, which is $6600 \, \Omega \pm 20\%$.

Table 8-2. Example Gain Error Factor and Gain Error for 10- Ω External Filter Input Resistors

DEVICE (GAIN)	GAIN ERROR FACTOR	GAIN ERROR (%)
A1 devices (20)	0.99658	−0.34185
A2 devices (50)	0.99598	−0.40141
A3 devices (100)	0.99598	−0.40141
A4 devices (200)	0.99499	−0.50051
A5 devices (500)	0.99203	−0.79663

8.2 Typical Application

The INA280 is a unidirectional, current-sense amplifier capable of measuring currents through a resistive shunt with shunt common-mode voltages from 2.7 V to 120 V. The circuit configuration for monitoring current in a high-side radio frequency (RF) power amplifier (PA) application is shown in Figure 8-2.

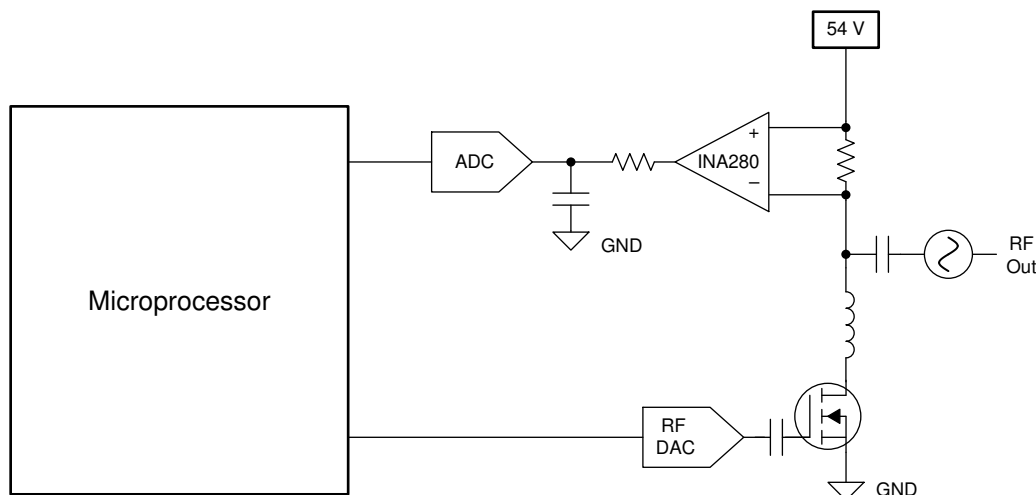


Figure 8-2. Current Sensing in a PA Application

8.2.1 Design Requirements

V_{SUPPLY} is set to 5 V, and the common-mode voltage set to 54 V. Table 8-3 lists the design setup for this application.

Table 8-3. Design Parameters

DESIGN PARAMETERS	EXAMPLE VALUE
INA280 supply voltage	5 V
High-side supply voltage	5 V
Maximum sense current (I_{MAX})	5 A
Gain option	50 V/V

8.2.2 Detailed Design Procedure

The maximum value of the current-sense resistor is calculated based choice of gain, value of the maximum current the be sensed (I_{MAX}), and the power-supply voltage (V_{S}). When operating at the maximum current, the output voltage must not exceed the positive output swing specification, V_{SP} . Under the given design parameters, Equation 6 calculates the maximum value for R_{SENSE} as 19.2 m Ω .

$$R_{\text{SENSE}} < \frac{V_{\text{SP}}}{I_{\text{MAX}} \times \text{GAIN}} \quad (6)$$

For this design example, a value of 15 m Ω is selected because, while the 15 m Ω is less than the maximum value calculated, 15 m Ω is still large enough to give adequate signal at the current-sense amplifier output.

8.2.2.1 Overload Recovery With Negative V_{SENSE}

The INA280 is a unidirectional current-sense amplifier that is meant to operate with a positive differential input voltage (V_{SENSE}). If negative V_{SENSE} is applied, the device is placed in an overload condition and requires time to recover once V_{SENSE} returns positive. The required overload recovery time increases with more negative V_{SENSE} .

8.2.3 Application Curve

Figure 8-3 shows the output response of the device to a high frequency sinusoidal current.

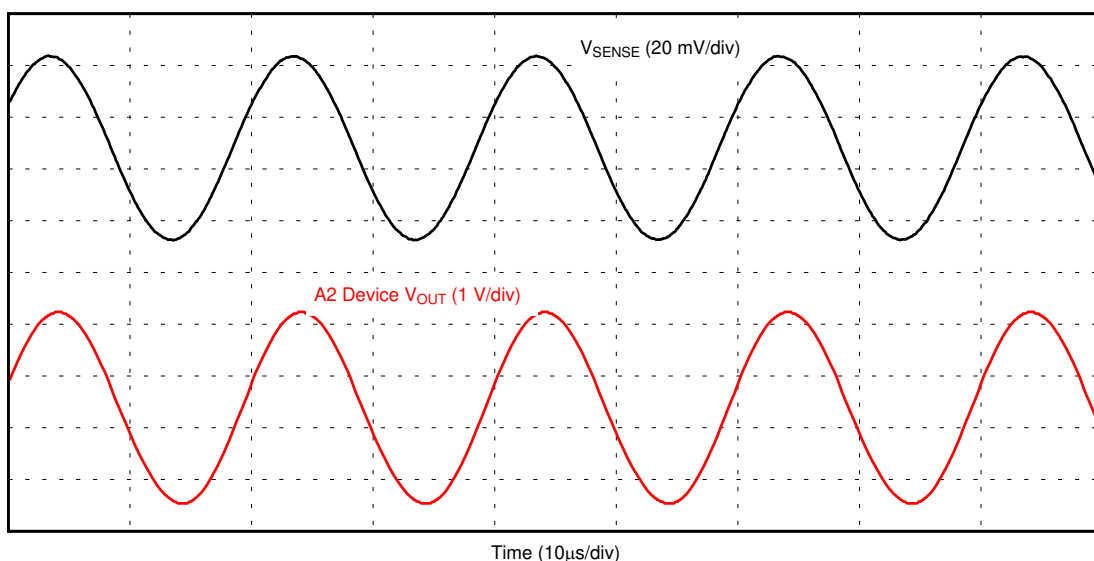


Figure 8-3. INA280 Output Response

9 Power Supply Recommendations

The input circuitry of the INA280 device can accurately measure beyond the power-supply voltage. The power supply can be 20 V, whereas the load power-supply voltage at IN+ and IN– can go up to 120 V. The output voltage range of the OUT pin is limited by the voltage on the V_S pin and the device swing to supply specification.

10 Layout

10.1 Layout Guidelines

TI always recommends to follow good layout practices:

- Connect the input pins to the sensing resistor using a Kelvin or 4-wire connection. This connection technique makes sure that only the current-sensing resistor impedance is detected between the input pins. Poor routing of the current-sensing resistor commonly results in additional resistance present between the input pins. Given the very low ohmic value of the current resistor, any additional high-current carrying impedance can cause significant measurement errors.
- Place the power-supply bypass capacitor as close to the device power supply and ground pins as possible. The recommended value of this bypass capacitor is 0.1 μF . Additional decoupling capacitance can be added to compensate for noisy or high-impedance power supplies.
- When routing the connections from the current-sense resistor to the device, keep the trace lengths as short as possible.

10.2 Layout Example

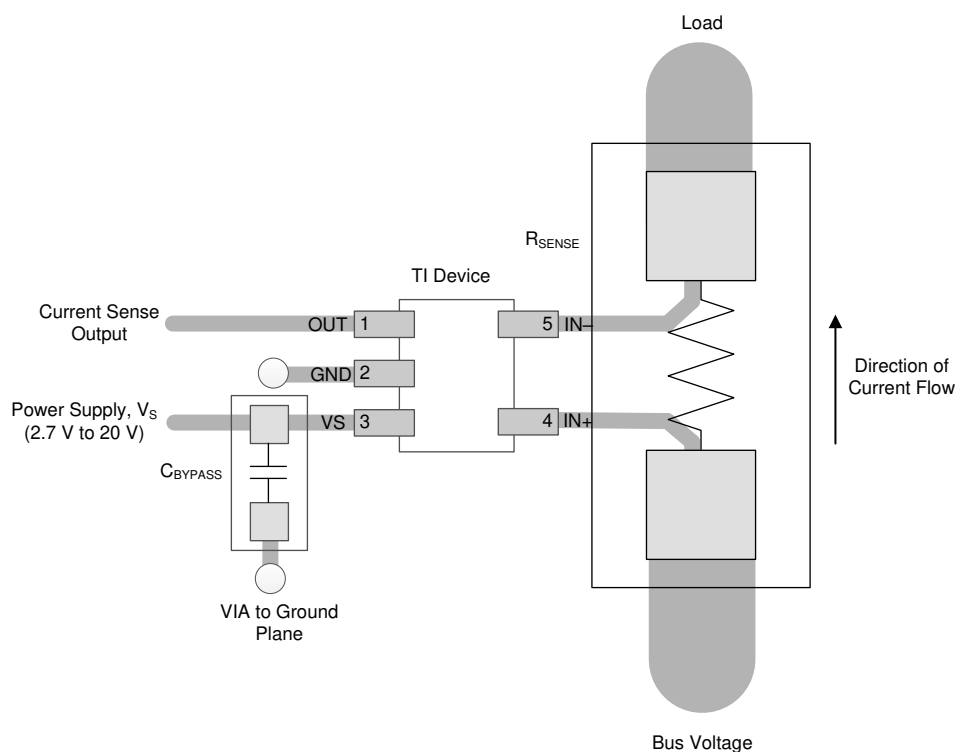


Figure 10-1. Recommended Layout for INA280

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation, see the following:

Texas Instruments, [INA280EVM User's Guide](#)

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](#). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Support Resources

[TI E2E™ support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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11.4 Trademarks

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11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
INA280A1IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HP	Samples
INA280A1IDCKT	LIFEBUY	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HP	
INA280A2IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HQ	Samples
INA280A2IDCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HQ	Samples
INA280A3IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HR	Samples
INA280A3IDCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HR	Samples
INA280A4IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HS	Samples
INA280A4IDCKT	LIFEBUY	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HS	
INA280A5IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HT	Samples
INA280A5IDCKT	LIFEBUY	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1HT	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF INA280 :

- Automotive : [INA280-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
INA280A1IDCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A1IDCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A2IDCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A2IDCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A3IDCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A3IDCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A4IDCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A4IDCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A5IDCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
INA280A5IDCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS

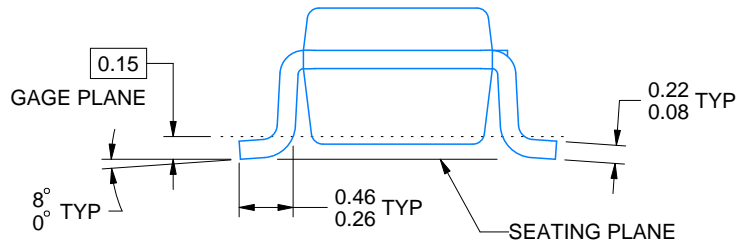
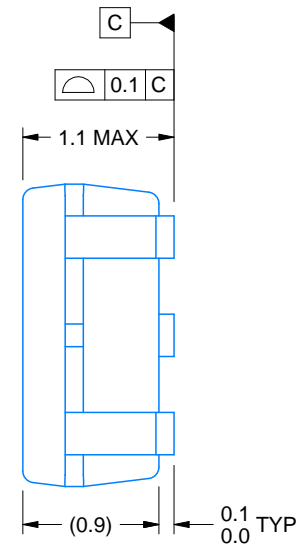


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
INA280A1IDCKR	SC70	DCK	5	3000	183.0	183.0	20.0
INA280A1IDCKT	SC70	DCK	5	250	183.0	183.0	20.0
INA280A2IDCKR	SC70	DCK	5	3000	183.0	183.0	20.0
INA280A2IDCKT	SC70	DCK	5	250	183.0	183.0	20.0
INA280A3IDCKR	SC70	DCK	5	3000	183.0	183.0	20.0
INA280A3IDCKT	SC70	DCK	5	250	183.0	183.0	20.0
INA280A4IDCKR	SC70	DCK	5	3000	183.0	183.0	20.0
INA280A4IDCKT	SC70	DCK	5	250	183.0	183.0	20.0
INA280A5IDCKR	SC70	DCK	5	3000	183.0	183.0	20.0
INA280A5IDCKT	SC70	DCK	5	250	183.0	183.0	20.0



SOT - 1.1 max height

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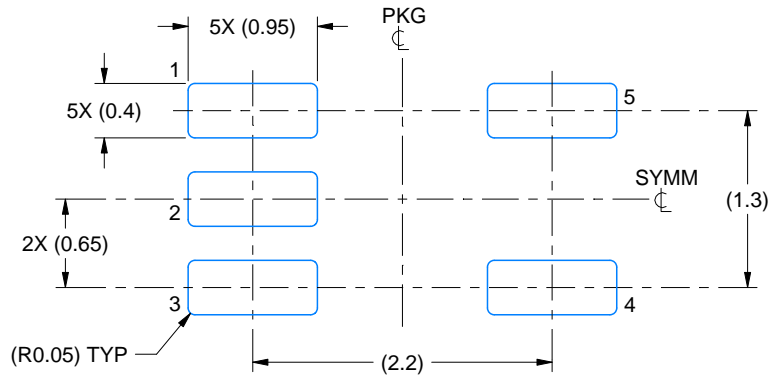
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

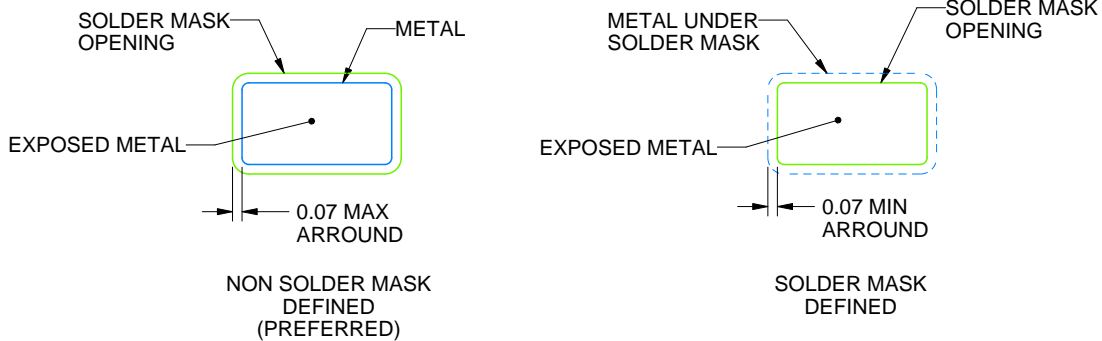
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

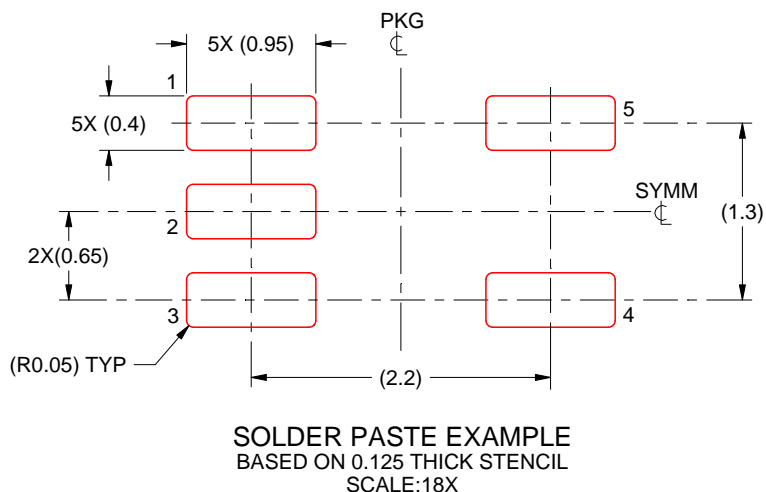


SOLDER MASK DETAILS

4214834/C 03/2023

NOTES: (continued)

4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



4214834/C 03/2023

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

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